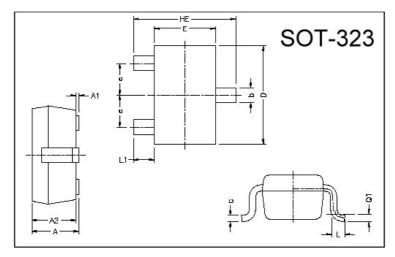
GS421SD

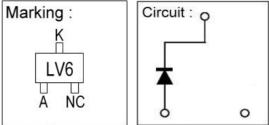
SURFACE MOUNT, SCHOTTKY BARRIER DIODE **VOLTAGE 40V, CURRENT 0.1A**

Description

The GS421SD is designed for low power rectification.

Package Dimensions





REF.	Milli	meter	REF.	Millimeter		
	Min.	Max.	nLI.	Min.	Max.	
Α	0.80	1.10	L1	0.42 REF.		
A1	0	0.10	L	0.15	0.35	
A2	0.80	1.00	b	0.25	0.40	
D	1.80	2.20	С	0.10	0.25	
Е	1.15	1.35	е	0.65 REF.		
HE	1.80	2.40	Q1	0.15 BSC.		

Absolute Maximum Ratings at TA = 25°C

Parameter	Symbol	Ratings	Unit ℃	
Junction Temperature	Tj	+125		
Storage Temperature	Tstg	-40 ~ +125	$^{\circ}$	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	V	
Maximum RMS Voltage	V_{RMS}	28	V	
Maximum DC Blocking Voltage	V_{DC}	40	V	
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	1.0	Α	
Typical Junction Capacitance between Terminal (Note 1)	CJ	6.0	pF	
Maximum Average Forward Rectified Current	lo	0.1	Α	
Total Power Dissipation	PD	225	mW	

Electrical Characteristics (at TA = 25°C unless otherwise noted)

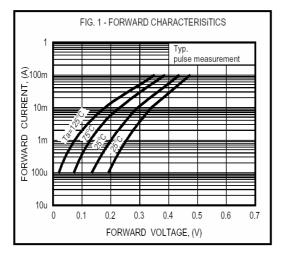
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)R	40	-	-	٧	IR=100μA
Maximum Instantaneous Forward Voltage	VF	ı	-	340	mV	IF1=10mA
waxiiiuiii iiistaiitaneous i olwaru voitage	VF	-	-	550		IF2=100mA
Maximum Average Reverse Current	lr	-	-	30	uA	VR=10V

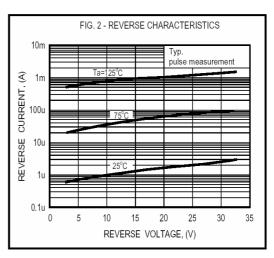
Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10 volts.

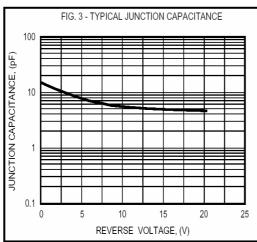
2. ESD sensitive product handling required.

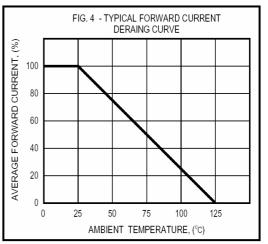
GS421SD Page: 1/2

Characteristics Curve









Important Notice:

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.

GTM reserves the right to make changes to its products without notice.

GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.

GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

GTM assumes no liability for any consequence of customer product design, infringement of patents, the Head Office And Factory:
 Taiwan: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
 TEL: 886-3-597-7061 FAX: 886-3-597-9220, 597-0785
 China: (201203) No.255, Jang-Jiang Tsai-Lueng RD., Pu-Dung-Hsin District, Shang-Hai City, China
 TEL: 86-21-5895-7671 ~ 4 FAX: 86-21-38950165

GS421SD Page: 2/2